



# XTSDG/Q0xG

## 3.3V/1.8V 1/2/4/8G-bit SD NAND Flash Memory Datasheet

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# SD NAND Flash Memory

## 3.3V/1.8V SD 2.0 Interface

### ■ 1/2/4/8G-bit SD NAND Flash Memory

- Based on Single-level cell (SLC) NAND technology
- Support 3.3V/1.8V voltage

### ■ SD Interface

- Compatible with SD 2.0
- Support 4bit SD mode, 1bit SPI mode
- Support default speed mode and high speed mode
- Support SD command class 0/2/4/5/6/7/8/10

### ■ High Performance

- 50MHz for high speed mode
- Sequential read up to 20MB/s
- Sequential write up to 4~6MB/s

### ■ Advanced NAND Management

- Built-in 14bits/512Byte hardware ECC engine
- Advanced bad block management
- Advanced wear leveling algorithm

### ■ Single Supply Voltage

- XTSDG0xG series: 2.7V~3.6V
- XTSDQ0xG series: 1.7~1.95V

### ■ Advanced Reliability Features

- Enhance power cycling support
- Industrial grade temperature range: -40~85°C

### ■ Package

- 8-pin WSON (8x6mm)
- 8-pin LGA(6x5mm) for 1.8V 1Gb/2Gb
- All Packages are RoHS Compliant and Halogen-free



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# 1. Introduction

XTX SD NAND is an embedded storage solution designed in a WSON8 package or a LGA8 package form. The operation of SD NAND is similar to a SD card which is an industry standard.

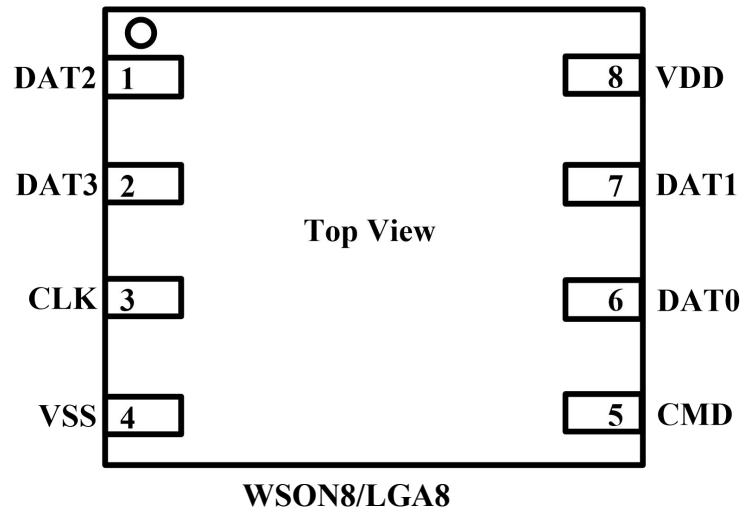
SD NAND consists of NAND flash and a high performance controller. Both 1.8V and 3.3V supply voltage series are supported.

XTX SD NAND is fully compliant with SD2.0 interface, which allows most of the embedded applications to easily adopt at a competitive cost with high reliability and low power consumption.

# 2. Ordering Part Number

OPN	Voltage Range	Capacity	Package Type	Package Carrier
XTSDG01GWSIGA	2.7-3.6V	1Gbit	WSON8 8x6mm	Tray
XTSDG02GWSIGA	2.7-3.6V	2Gbit	WSON8 8x6mm	Tray
XTSDG04GWSIGA	2.7-3.6V	4Gbit	WSON8 8x6mm	Tray
XTSDG08GWSIGA	2.7-3.6V	8Gbit	WSON8 8x6mm	Tray
XTSDQ01GWSIGA	1.7-1.95V	1Gbit	WSON8 8x6mm	Tray
XTSDQ02GWSIGA	1.7-1.95V	2Gbit	WSON8 8x6mm	Tray
XTSDQ04GWSIGA	1.7-1.95V	4Gbit	WSON8 8x6mm	Tray
XTSDQ08GWSIGA	1.7-1.95V	8Gbit	WSON8 8x6mm	Tray
XTSDQ01GLAIGA	1.7-1.95V	1Gbit	LGA8 6x5mm	Tray
XTSDQ02GLAIGA	1.7-1.95V	2Gbit	LGA8 6x5mm	Tray

### 3. Pin Assignments



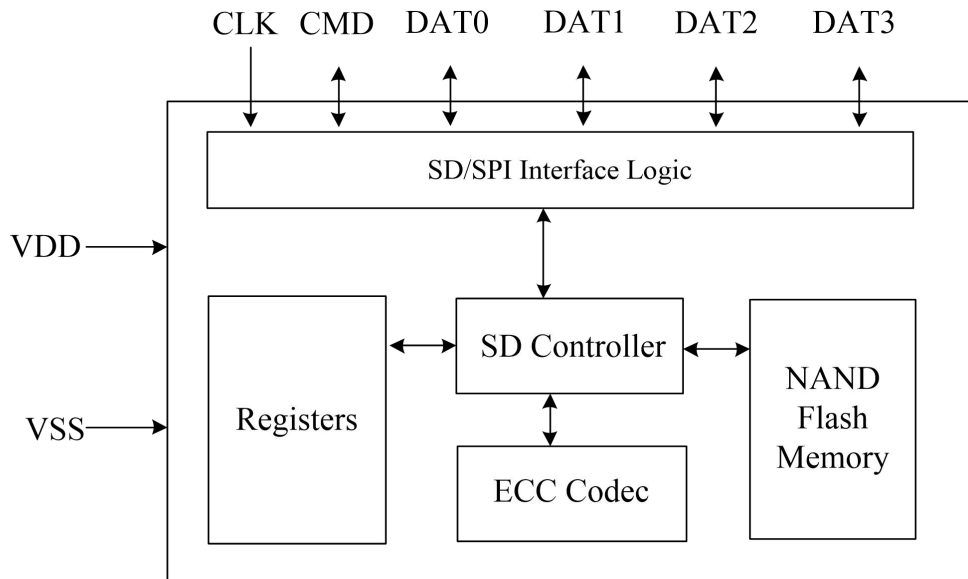
#### 3.1 Pin Description

Pin #	SD Interface			SPI Interface		
	Pin Name	Type	Description	Pin Name	Type	Description
1	DAT2	I/O/PP	Data Line [bit2]	Reserved	Reserved	Reserved
2	DAT3/CD	I/O/PP	Data Line[bit3] / SD NAND Detection	CS	I	Chip Select
3	CLK	I	Clock	CLK	I	Clock
4	VSS	S	Ground	VSS	S	Ground
5	CMD	PP	Command/Response	DI	I	Data in
6	DAT0	I/O/PP	Data Line [bit0]	DO	O/PP	Data out
7	DAT1	I/O/PP	Data Line [bit1]	Reserved	Reserved	Reserved
8	VDD	S	Supply voltage	VDD	S	Supply voltage

**Notes:**

1. S: power supply; I: input; O: output; PP: I/O using push-pull drivers.
2. The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after SET\_BUS\_WIDTH command.

## 4. Block Diagram



# 5. Product Specification

## 5.1 System Performance

OPN	Voltage Range	Sequential Read Performance (MB/s)	Sequential Write Performance (MB/s)
XTSDG01GWSIGA	2.7-3.6V	20	4
XTSDG02GWSIGA	2.7-3.6V	20	4
XTSDG04GWSIGA	2.7-3.6V	20	6
XTSDG08GWSIGA	2.7-3.6V	20	6
XTSDQ01GWSIGA XTSDQ01GLAIGA	1.7-1.95V	20	4
XTSDQ02GWSIGA XTSDQ02GLAIGA	1.7-1.95V	20	4
XTSDQ04GWSIGA	1.7-1.95V	20	6
XTSDQ08GWSIGA	1.7-1.95V	20	6

## 5.2 Timeout Error Conditions

Timing	Max. Value
Block Read Access Timeout	100ms
Block Write Access Timeout	250ms
Initialization Timeout(ACMD 41) <sup>1</sup>	1s

**Notes:**

1.The host shall set ACMD41 timeout more than 1 second to abort repeat of issuing ACMD41 when the SD NAND does not indicate ready. The timeout count starts from the first ACMD41 which is set voltage window in the argument.

## 5.3 Registers

Six registers are defined within the SD interface: OCR, CID, CSD, RCA, DSR and SCR. These can be accessed only by corresponding commands.

The OCR, CID, CSD and SCR registers carry the specific information, while the RCA and DSR registers are configuration registers storing actual configuration parameters. OCR Register, the 32-bit operation conditions register stores the VDD voltage profile of the card. Additionally, this register includes status information bits.

### 5.3.1 OCR Register

OCR Register Definition - 3.3V

OCR bit	VDD Voltage Window	OCR Value
0 - 6	Reserved	All "0"
7	Reserved for low voltage range	0
8 - 14	Reserved	All "0"
15	2.7 - 2.8	1
16	2.8 - 2.9	1
17	2.9 - 3.0	1
18	3.0 - 3.1	1
19	3.1 - 3.2	1
20	3.2 - 3.3	1
21	3.3 - 3.4	1
22	3.4 - 3.5	1
23	3.5 - 3.6	1
24 - 29	Reserved	All "0"
30	Card Capacity status(CCS) <sup>1</sup>	0
31	Card power up status bit(busy) <sup>2</sup>	"0" = busy , "1" = ready

**Notes:**

1. This bit is valid only when the power up status bit is set.
2. This bit is set to LOW if the SD NAND has not finished the power up routine.





## OCR Register Definition - 1.8V

OCR bit	VDD Voltage Window	OCR Value
0 - 6	Reserved	All "0"
7	Reserved for low voltage range	0
8 - 14	Reserved	All "0"
15	2.7 - 2.8	0
16	2.8 - 2.9	0
17	2.9 - 3.0	0
18	3.0 - 3.1	0
19	3.1 - 3.2	0
20	3.2 - 3.3	0
21	3.3 - 3.4	0
22	3.4 - 3.5	0
23	3.5 - 3.6	0
24 - 29	Reserved	All "0"
30	Card Capacity status(CCS) <sup>1</sup>	0
31	Card power up status bit(busy) <sup>2</sup>	"0" = busy , "1" = ready

**Notes:**

1. This bit is valid only when the power up status bit is set.
2. This bit is set to LOW if the SD NAND has not finished the power up routine.

### 5.3.2 CID Register

The Card Identification (CID) register is 128 bits wide. It contains the card identification information used during the card identification phase. It is programmed during manufacturing and cannot be changed by hosts.

The structure of the CID register is defined in the following paragraphs:

CID Register Fields

Name	Field	Type	Width	CID Value			
				1Gb	2Gbit	4Gb	8Gb
Manufacturer ID	MID	Binary	8	TBD			
OEM/Application ID	OID	ASCII	16	TBD			
Product name	PNM	ASCII	40	TBD			
Product revision	PRV	BCD	8	TBD			
Product serial number	PSN	Binary	32	Controlled by Production Lot			
Reserved	-	-	4	All "0"			
Manufacturing date	MDT	BCD	12	Manufacture date			
CRC7 checksum	CRC	Binary	7	CRC			
not used, always '1'	-	-	1	1b			

### 5.3.3 CSD Register

The Card-Specific Data register provides information on how to access the SD NAND contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register can be changed by CMD27. The type of the entries in the table below is coded as follows: R = readable, W=multiple writable.

The CSD Register Fields (CSD Version 1.0)

Name	Field	Width	Cell Type	CSD-slice	CSD Value			
					1Gb	2Gb	4Gb	8Gb
CSD structure	CSD_STRUCTURE	2	R	[127:126]	00b			
Reserved	-	6	R	[125:120]	000000b			
Data read access-time 1	TAAC	8	R	[119:112]	7Fh			
Data read access-time 2 In CLK cycles(NSAC*100)	NSAC	8	R	[111:104]	00h			
Max. data transfer rate	TRAN_SPEED	8	R	[103:96]	32h			
Card command classes	CCC	12	R	[95:84]	010110110101b			
Max. read data block length	READ_BL_LEN	4	R	[83:80]	1001b			1010b
Partial blocks for read allowed	READ_BL_PARTIAL	1	R	[79:79]	1b			
Write block misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]	0b			
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]	0b			
DSR implemented	DSR_IMP	1	R	[[76:76]	0b			
Reserved	-	2	R	[75:74]	00b			
Device size	C_SIZE	12	R	[73:62]	TBD	TBD	TBD	TBD
Max. read current @ VDD min	VDD_R_CURR_MIN	3	R	[61:59]	101b			
Max. read current @ VDD max	VDD_R_CURR_MAX	3	R	[58:56]	110b			
Max. write current @ VDD min	VDD_W_CURR_MIN	3	R	[55:53]	101b			
Max. write current @ VDD max	VDD_W_CURR_MAX	3	R	[52:50]	110b			
Device size multiplier	C_SIZE_MULT	3	R	[49:47]	110b			
Erase single block enable	ERASE_BLK_EN	1	R	[46:46]	1b			
Erase sector size	SECTOR_SIZE	7	R	[45:39]	1111111b			
Write protect group size	WP_GRP_SIZE	7	R	[38:32]	0011111b			
Write protect group enable	WP_GRP_ENABLE	1	R	[31:31]	1b			
Reserved	-	2	R	[30:29]	00b			
Write speed factor	R2W_FACTOR	3	R	[28:26]	101b			
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]	1001b			1010b
Partial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]	0b			
Reserved	-	5	R	[20:16]	00000b			
File format group	FILE_FORMAT_GRP	1	R	[15:15]	0b			
Copy flag (OTP)	COPY	1	R	[14:14]	0b			
Permanent write protection	PERM_WRITE_PROTECT	1	R	[13:13]	0b			
Temporary write protection	TMP_WRITE_PROTECT	1	R/W	[12:12]	0b			
File format	FILE_FORMAT	2	R	[11:10]	00b			
Reserved	-	2	R	[9:8]	00b			
CRC	CRC	7	R	[7:1]	xxxxxxx			
Not used, always '1'	-	1	-	[0:0]	1b			



### 5.3.4 RCA Register

The writable 16-bit relative card address register carries the card address that is published by the card during the card identification. This address is used for the addressed host-card communication after the card identification procedure. The default value of the RCA register is 0x0000. The value 0x0000 is reserved to set all cards into the Stand-by State with CMD7.

### 5.3.5 SCR Register

In addition to the CSD register, there is another configuration register named SD CARD Configuration Register (SCR). SCR provides information on the SD NAND’s special features. The following table describes the SCR register content.

The SCR Fields

Name	Field	Width	Cell Type	CSD-slice	CSD Value			
					1Gb	2Gb	4Gb	8Gb
SCR structure	SCR_STRUCTURE	4	R	[63:60]	000b			
SD Memory Card - Spec. Version	SD_SPEC	4	R	[59:56]	0010b			
Data_Status_after_Erases	DATA_STAT_AFTER_ERASE	1	R	[55:55]	1b			
SD Security Support	SD_SECURITY	3	R	[54:52]	010b			
DAT Bus Widths Supported	SD_BUS_WIDTHS	4	R	[51:48]	0101b			
Reserved	-	16	R	[46:34]	-			
Reserved for Manufacturer Usage	-	32	R	[31:0]	-			

# 6. Command

## 6.1 SD Mode Command

SD Mode Command Set (+: Implemented -: Not Implemented)

CMD	Abbreviation	Implementation	Notes
CMD0	GO_IDLE_STATE	+	
CMD2	ALL_SEND_CID	+	
CMD3	SEND_RELATIVE_ADDR	+	
CMD4	SET_DSR	-	DSR register is not implemented
CMD6	SWITCH_FUNC	+	
CMD7	SELECT/DESELECT_CARD	+	
CMD8	SEND_IF_COND	+	
CMD9	SEND_CSD	+	
CMD10	SEND_CID	+	
CMD12	STOP_TRANSMISSION	+	
CMD13	SEND_STATUS	+	
CMD15	GO_INACTIVE_STATE	+	
CMD16	SET_BLOCKLEN	+	
CMD17	READ_SINGLE_BLOCK	+	
CMD18	READ_MULTIPLE_BLOCK	+	
CMD24	WRITE_BLOCK	+	
CMD25	WRITE_MULTIPLE_BLOCK	+	
CMD27	PROGRAM_CSD	+	
CMD28	SET_WRITE_PROT	+	
CMD29	CLR_WRITE_PROT	+	
CMD30	SEND_WRITE_PROT	+	
CMD32	ERASE_WR_BLK_START	+	
CMD33	ERASE_WR_BLK_END	+	
CMD38	ERASE	+	
CMD42	LOCK_UNLOCK	+	
CMD55	APP_CMD	+	
CMD56	GEN_CMD	-	This command is for vendor-specific
ACMD6	SET_BUS_WIDTH	+	
ACMD13	SD_STATUS	+	
ACMD22	SEND_NUM_WR_BLOCKS	+	
ACMD23	SET_WR_BLK_ERASE_COUNT	+	
ACMD41	SD_APP_OP_COND	+	
ACMD42	SET_CLR_CARD_DETECT	+	
ACMD51	SEND_SCR	+	
ACMD18	SECURE_READ_MULTI_BLOCK	-	
ACMD25	SECURE_WRITE_MULTI_BLOCK	-	
ACMD26	SECURE_WRITE_MKB	-	
ACMD38	SECURE_ERASE	-	
ACMD43	GET_MKB	-	
ACMD44	GET_MID	-	
ACMD45	SET_CER_RN1	-	
ACMD46	SET_CER_RN2	-	
ACMD47	SET_CER_RES2	-	
ACMD48	SET_CER_RES1	-	
ACMD49	CHANGE_SECURE_AREA	-	

## 6.2 SPI Mode Command

SPI Mode Command Set (+: Implemented -: Not Implemented)

CMD	Abbreviation	Implementatio	Notes
CMD0	GO_IDLE_STATE	+	
CMD1	SEND_OP_CND	+	
CMD6	SWITCH_FUNC	+	
CMD8	SEND_IF_COND	+	
CMD9	SEND_CSD	+	
CMD10	SEND_CID	+	
CMD12	STOP_TRANSMISSION	+	
CMD13	SEND_STATUS	+	
CMD16	SET_BLOCKLEN	+	
CMD17	READ_SINGLE_BLOCK	+	
CMD18	READ_MULTIPLE_BLOCK	+	
CMD24	WRITE_BLOCK	+	
CMD25	WRITE_MULTIPLE_BLOCK	+	
CMD27	PROGRAM_CSD	+	
CMD28	SET_WRITE_PROT	+	
CMD29	CLR_WRITE_PROT	+	
CMD30	SEND_WRITE_PROT	+	
CMD32	ERASE_WR_BLK_START_ADD	+	
CMD33	ERASE_WR_BLK_END_ADDR	+	
CMD38	ERASE	+	
CMD42	LOCK_UNLOCK	+	
CMD55	APP_CMD	+	
CMD56	GEN_CMD	-	This command is for vendor-specific
CMD58	READ_OCR	+	
CMD59	CRC_ON_OFF	+	
ACMD13	SD_STATUS	+	
ACMD22	SEND_NUM_WR_BLOCKS	+	
ACMD23	SET_WR_BLK_ERASE_COUNT	+	
ACMD41	SD_APP_OP_COND	+	
ACMD42	SET_CLR_CARD_DETECT	+	
ACMD51	SEND_SCR	+	
ACMD18	SECURE_READ_MULTI_BLOC	-	
ACMD25	SECURE_WRITE_MULTI_BLO	-	
ACMD26	SECURE_WRITE_MKB	-	
ACMD38	SECURE_ERASE	-	
ACMD43	GET_MKB	-	
ACMD44	GET_MID	-	
ACMD45	SET_CER_RN1	-	
ACMD46	SET_CER_RN2	-	
ACMD47	SET_CER_RES2	-	
ACMD48	SET_CER_RES1	-	
ACMD49	CHANGE_SECURE_AREA	-	

# 7. Electrical Characteristics

## 7.1 Absolute Maximum Ratings

Operating Temperature	-40°C to +85°C
Storage Temperature	-55°C to +125°C
Voltage on I/O Pin with Respect to Ground(XTSDG0x Series)	-0.3V to VDD+0.3V (<= 3.9V)
Voltage on I/O Pin with Respect to Ground(XTSDQ0x Series)	-0.3V to VDD+0.3V (<= 2.25V)
V <sub>DD</sub> (XTSDG0x Series)	-0.3V to 3.9V
V <sub>DD</sub> (XTSDQ0x Series)	-0.3V to 2.25V

**Notes:**

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## 7.2 Bus Signal Line Load

The total capacitance C<sub>L</sub> of each line of the SD NAND bus is the sum of the bus master capacitance C<sub>HOST</sub>, the bus capacitance C<sub>BUS</sub> itself and the capacitance C<sub>CARD</sub> of each card connected to this line:

$$C_L = C_{HOST} + C_{BUS} + N * C_{CARD}$$

Where N is the number of connected SD NAND/Cards.

Symbol	Parameter	Min.	Max.	Units	Remark
C <sub>L</sub>	Total bus capacitance for each signal line		40	pF	C <sub>HOST</sub> +C <sub>BUS</sub> <= 30pF
C <sub>CARD</sub> <sup>(1)</sup>	Single card capacitance		10	pF	
R <sub>CMD</sub>	Pull-up resistance	10	100	K Ohm	Prevent bus floating
	Maximum signal line inductance		16	nH	f <sub>PP</sub> <= 20MHz
R <sub>DAT3</sub>	Pull-up resistance inside card(pin1)	10	90	K Ohm	May be used for card detection
C <sub>C</sub> <sup>(2)</sup>	Capacity connected to power line		5	uF	To prevent inrush current

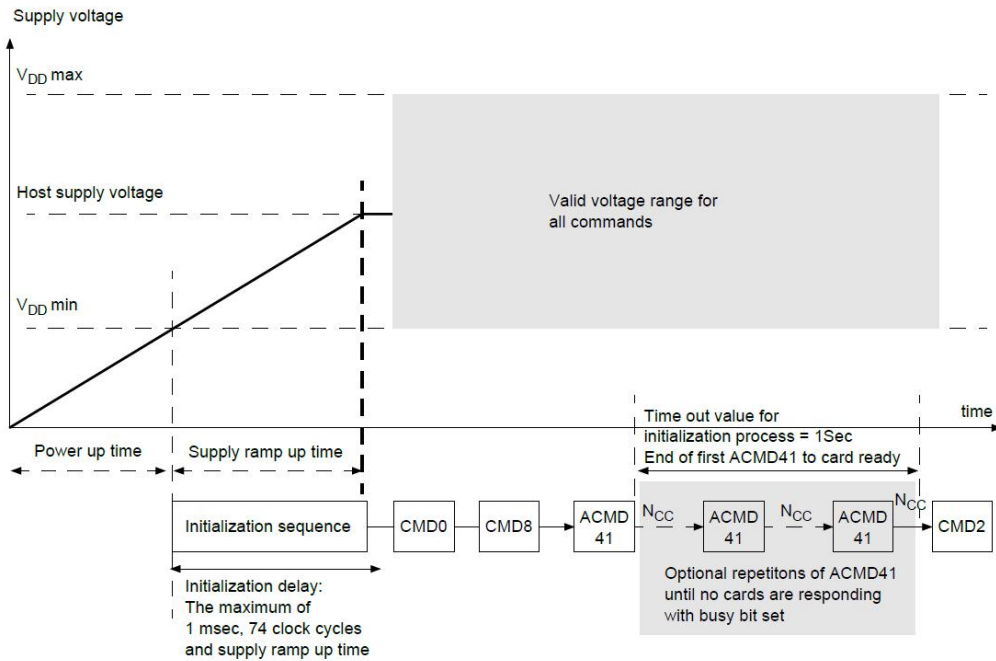
**Notes:**

1. Characterized and is not 100% tested.
2. To limit inrush current caused by host insertion, card maximum capacitance between VDD - VSS is defined as 5uF. To support host hot insertion, the host should consider decoupling capacitor connected to power line. As SD NAND C<sub>c</sub> is 5uF (Max.), 45uF (min.) is recommended for Decoupling capacitor.



### 7.3 Power-up

The power-up of the SD NAND bus is handled locally in each SD NAND and in the host.



Power up time is defined as voltage rising time from 0 volt to VDD(min.) and depends on application parameters such as the maximum number of SD NAND/Cards, the bus length and the characteristic of the power supply unit.

Supply ramp up time provides the time that the power is built up to the operating level (the host supply voltage) and the time to wait until the SD NAND can accept the first command.

The host shall supply power to the SD NAND so that the voltage is reached to VDD (min.) within 250ms and start to supply at least 74 SD clocks to the SD NAND with keeping CMD line to high. In case of SPI mode, CS shall be held to high during 74 clock cycles.

After power up the SD NAND enters the idle state. In case of SD host, CMD0 is not necessary. In case of SPI host, CMD0 shall be the first command to send the card to SPI mode.

CMD8 is to support multiple voltage ranges and used to check whether the card supports supplied voltage. The host that does not support CMD8 shall supply high voltage range.

ACMD41 is a synchronization command used to negotiate the operation voltage range and to poll the SD NAND until they are out of their power-up sequence.

## 7.4 DC Electrical Characteristics

### DC Characteristics – 3.3V

Applicable over recommended operating range from: TA = -40°C to 85°C, VDD = 2.7V to 3.6 V, (unless otherwise noted)

SYMBOL	PARAMETER	CONDITIONS	SPEC			UNIT
			MIN.	TYP.	MAX.	
VDD	Supply Voltage		2.7		3.6	V
ILI	Input Leakage Current		-2		2	μA
ILO	Output Leakage Current		-2		2	μA
ICC1	Standby Current	VDD=3.6V		130	2500 <sup>(2)</sup>	μA
ICC2	Read Current	FCLK=50MHz		32	75	mA
	Write Current			32	75	mA
VIL (1)	Input Low Voltage		-0.3		0.3VDD	V
VIH	Input High Voltage		0.7VDD		VDD+0.3	V
VOL	Output Low Voltage	IOL = 2mA VDD min			0.4	V
VOH	Output High Voltage	IOH = -2mA VDD min	VDD-0.3			V

**Notes:**

1. VIL min and VIH max are reference only and are not tested.
2. Standby Current at Ta=-40°C-70°C will not exceed 1300μA.

**DC Characteristics – 1.8V**

Applicable over recommended operating range from: TA = -40°C to 85°C, VDD = 1.7V to 1.95 V, (unless otherwise noted)

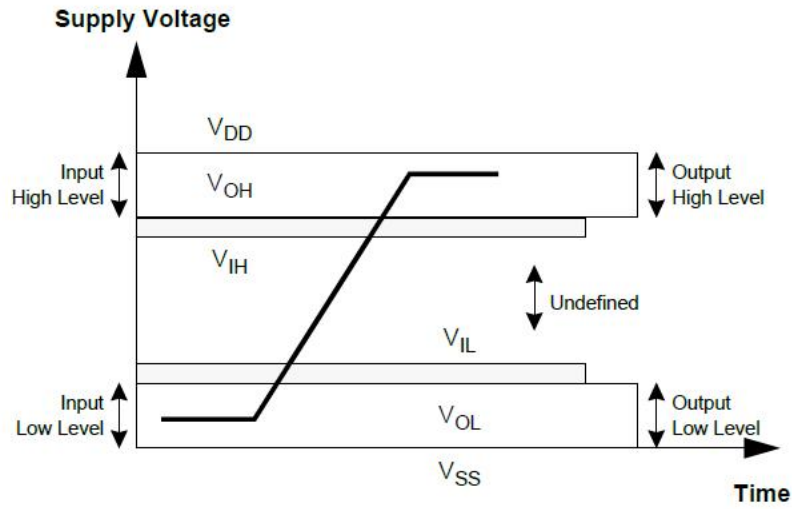
SYMBOL	PARAMETER	CONDITIONS	SPEC			UNIT
			MIN.	TYP.	MAX.	
VDD	Supply Voltage		1.7		1.95	V
ILI	Input Leakage Current		-2		2	μA
ILO	Output Leakage Current		-2		2	μA
ICC1	Standby Current	VDD=1.95V		130	2500(2)	μA
ICC2	Read Current	FCLK=50MHz		32	75	mA
	Write Current			32	75	mA
VIL (1)	Input Low Voltage		-0.3		0.3VDD	V
VIH	Input High Voltage		0.7VDD		VDD+0.3	V
VOL	Output Low Voltage	IOL = 2mA			0.4	V
VOH	Output High Voltage	IOH = -2mA	VDD-0.3			V

**Notes:**

1. VIL min and VIH max are reference only and are not tested.
2. Standby Current at Ta=-40°C-70°C will not exceed 1300μA.

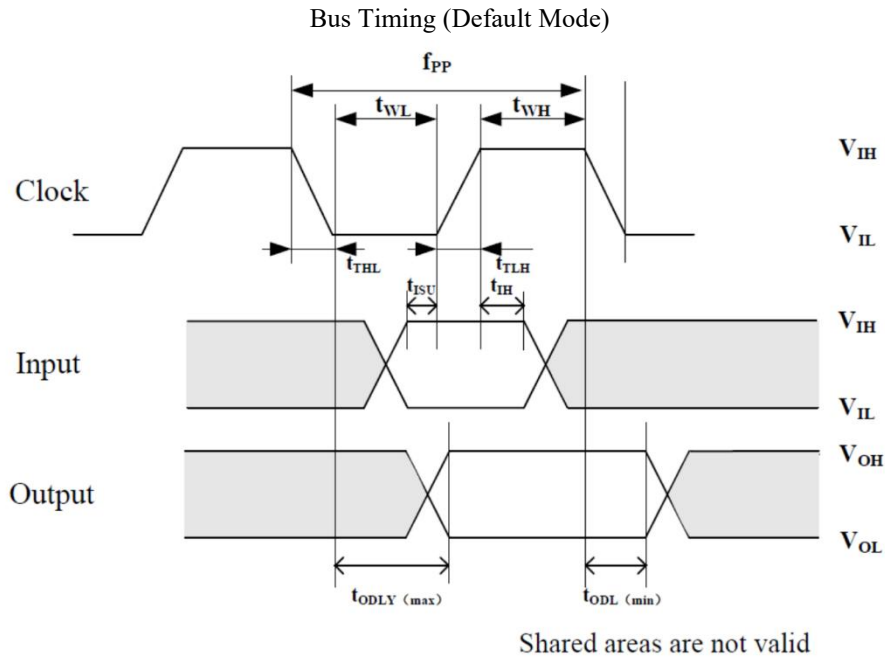
## 7.5 Bus Signal Levels

As the bus can be supplied with a variable supply voltage, all signal levels are related to the supply voltage.



To meet the requirements of the JEDEC specification JESD8-1A and JESD8-7, the card input and output voltages shall be within the specified ranges for any V<sub>DD</sub> of the allowed voltage range.

## 7.6 AC Electrical Characteristics



### AC Characteristics – Default Mode – 3.3V

Applicable over recommended operating range from: TA = -40°C to 85°C, VDD = 2.7V to 3.6V, CL = 30pF

SYMBOL	PARAMETER	SPEC			UNIT
		MIN.	TYP.	MAX.	
Clock CLK (All values are referred to min. (VIH) and max. (VIL))					
f <sub>PP</sub>	Clock frequency Data Transfer Mode			25	MHz
f <sub>OD</sub>	Clock frequency Identification Mode	0 <sup>1</sup> / 100		400	KHz
t <sub>WL</sub>	Clock low time	10			ns
t <sub>WH</sub>	Clock high time	10			ns
t <sub>TLH</sub>	Clock rise time			10	ns
t <sub>THL</sub>	Clock fall time			10	ns
Inputs CMD, DAT (referenced to CLK)					
t <sub>ISU</sub>	Input setup time	5			ns
t <sub>IH</sub>	Input hold time	5			ns
Outputs CMD, DAT (referenced to CLK)					
t <sub>ODLY</sub>	Output delay time during Data Transfer Mode	0		14	ns
t <sub>ODLY</sub>	Output delay time during Identification Mode	0		50	ns

**Notes:**

1.0Hz means to stop the clock. The given minimum frequency range is for cases where a continuous clock is required.



## AC Characteristics – Default Mode – 1.8V

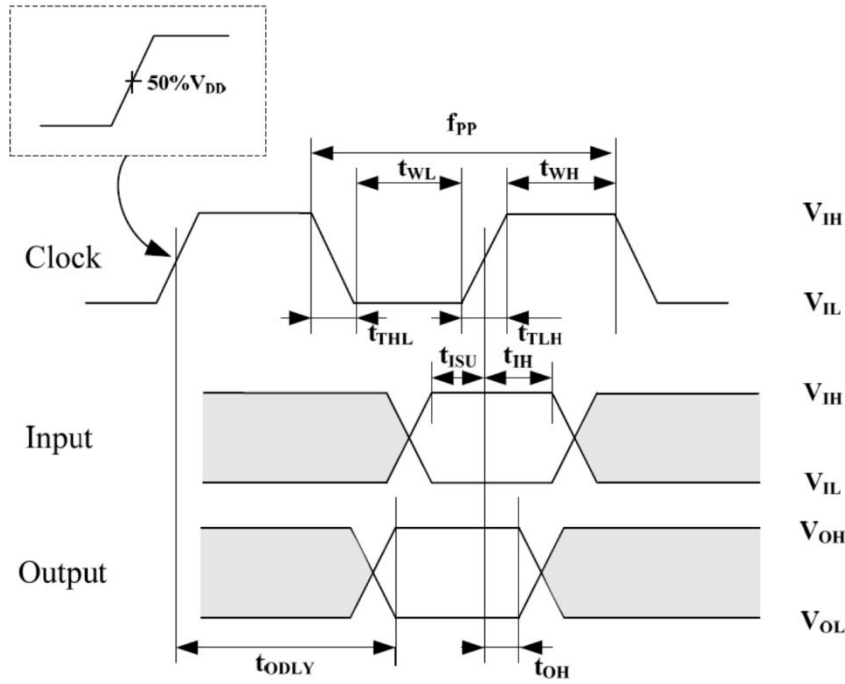
Applicable over recommended operating range from: TA = -40°C to 85°C, VDD = 1.7V to 1.95V, CL = 30pF

SYMBOL	PARAMETER	SPEC			UNIT
		MIN.	TYP.	MAX.	
Clock CLK (All values are referred to min. (VIH) and max. (VIL) )					
f <sub>PP</sub>	Clock frequency Data Transfer Mode			25	MHz
f <sub>OD</sub>	Clock frequency Identification Mode	0 <sup>1</sup> / 100		400	KHz
t <sub>WL</sub>	Clock low time	10			ns
t <sub>WH</sub>	Clock high time	10			ns
t <sub>TLH</sub>	Clock rise time			10	ns
t <sub>THL</sub>	Clock fall time			10	ns
Inputs CMD, DAT (referenced to CLK)					
t <sub>ISU</sub>	Input setup time	5			ns
t <sub>IH</sub>	Input hold time	5			ns
Outputs CMD, DAT (referenced to CLK)					
t <sub>ODLY</sub>	Output delay time during Data Transfer Mode	0		14	ns
t <sub>ODLY</sub>	Output delay time during Identification Mode	0		50	ns

**Notes:**

1.0Hz means to stop the clock. The given minimum frequency range is for cases where a continuous clock is required.

Bus Timing (High-speed Mode)



AC Characteristics – High-Speed Mode – 3.3V

Applicable over recommended operating range from:  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ ,  $V_{DD} = 2.7V$  to  $3.6V$ ,  $C_L = 30pF$

SYMBOL	PARAMETER	SPEC			UNIT
		MIN.	TYP.	MAX.	
Clock CLK (All values are referred to min. (VIH) and max. (VIL) )					
$f_{PP}$	Clock frequency Data Transfer Mode			50	MHz
$t_{WL}$	Clock low time	7			ns
$t_{WH}$	Clock high time	7			ns
$t_{TLH}$	Clock rise time			3	ns
$t_{THL}$	Clock fall time			3	ns
Inputs CMD, DAT (referenced to CLK)					
$t_{ISU}$	Input setup time	6			ns
$t_{IH}$	Input hold time	2			ns
Outputs CMD, DAT (referenced to CLK)					
$t_{ODLY}$	Output delay time during Data Transfer Mode	0		14	ns
$t_{OH}$	Output Hold time	2.5			ns
$C_L$	Total system capacitance for each line <sup>1</sup>			40	pF

Notes:

- In order to satisfy severe timing, host shall drive only one SD NAND.

**AC Characteristics – High-Speed Mode – 1.8V**

Applicable over recommended operating range from: TA = -40°C to 85°C, VDD = 1.7V to 1.95V, CL = 30pF

SYMBOL	PARAMETER	SPEC			UNIT
		MIN.	TYP.	MAX.	
Clock CLK (All values are referred to min. (VIH) and max. (VIL) )					
f <sub>PP</sub>	Clock frequency Data Transfer Mode			50	MHz
t <sub>WL</sub>	Clock low time	7			ns
t <sub>WH</sub>	Clock high time	7			ns
t <sub>TLH</sub>	Clock rise time			3	ns
t <sub>THL</sub>	Clock fall time			3	ns
Inputs CMD, DAT (referenced to CLK)					
t <sub>ISU</sub>	Input setup time	6			ns
t <sub>IH</sub>	Input hold time	2			ns
Outputs CMD, DAT (referenced to CLK)					
t <sub>ODLY</sub>	Output delay time during Data Transfer Mode	0		14	ns
t <sub>OH</sub>	Output Hold time	2.5			ns
CL	Total system capacitance for each line <sup>1</sup>			40	pF

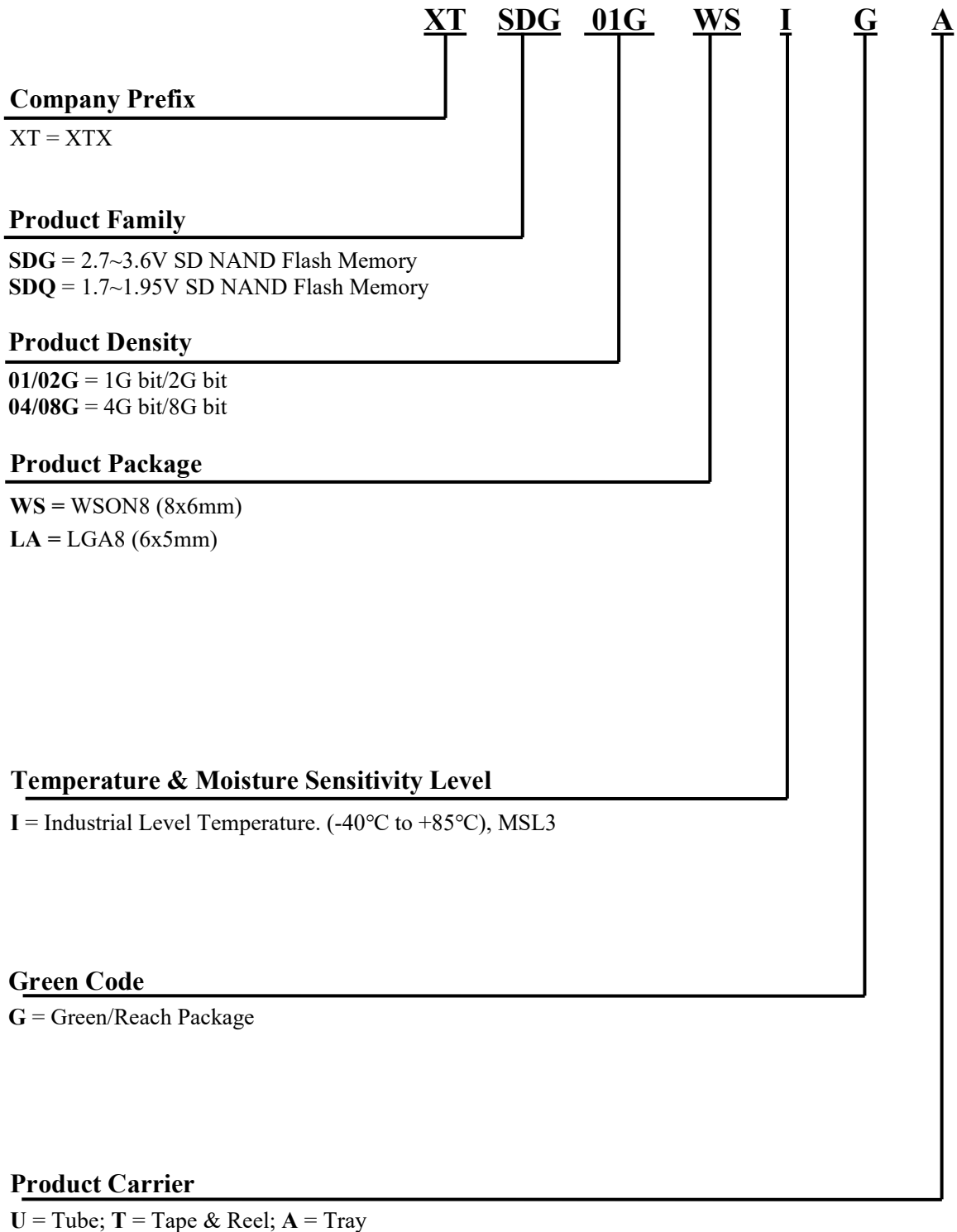
**Notes:**

1. In order to satisfy severe timing, host shall drive only one SD NAND.



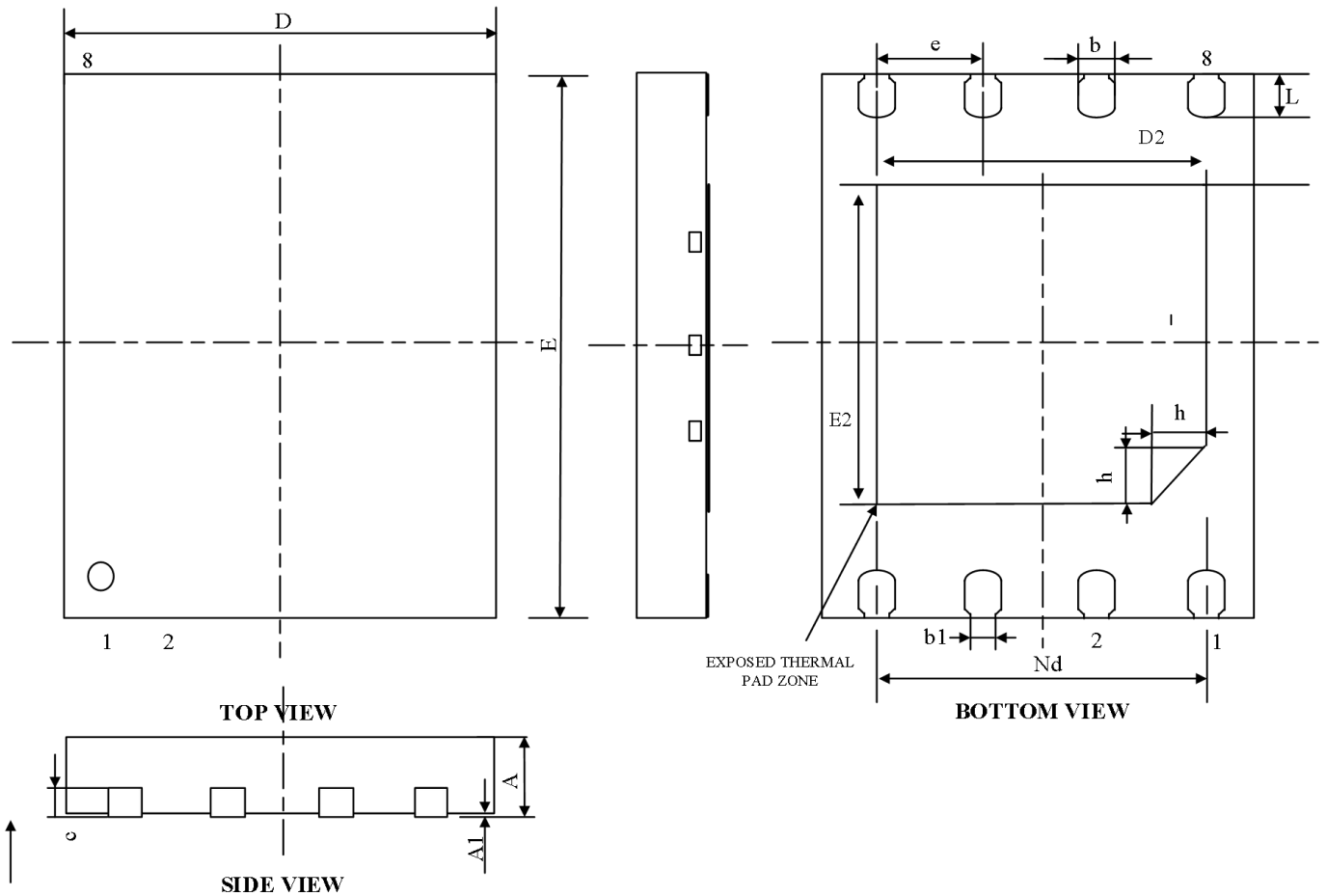
## 8. Part Numbering

The ordering part number is formed by a valid combination of the following



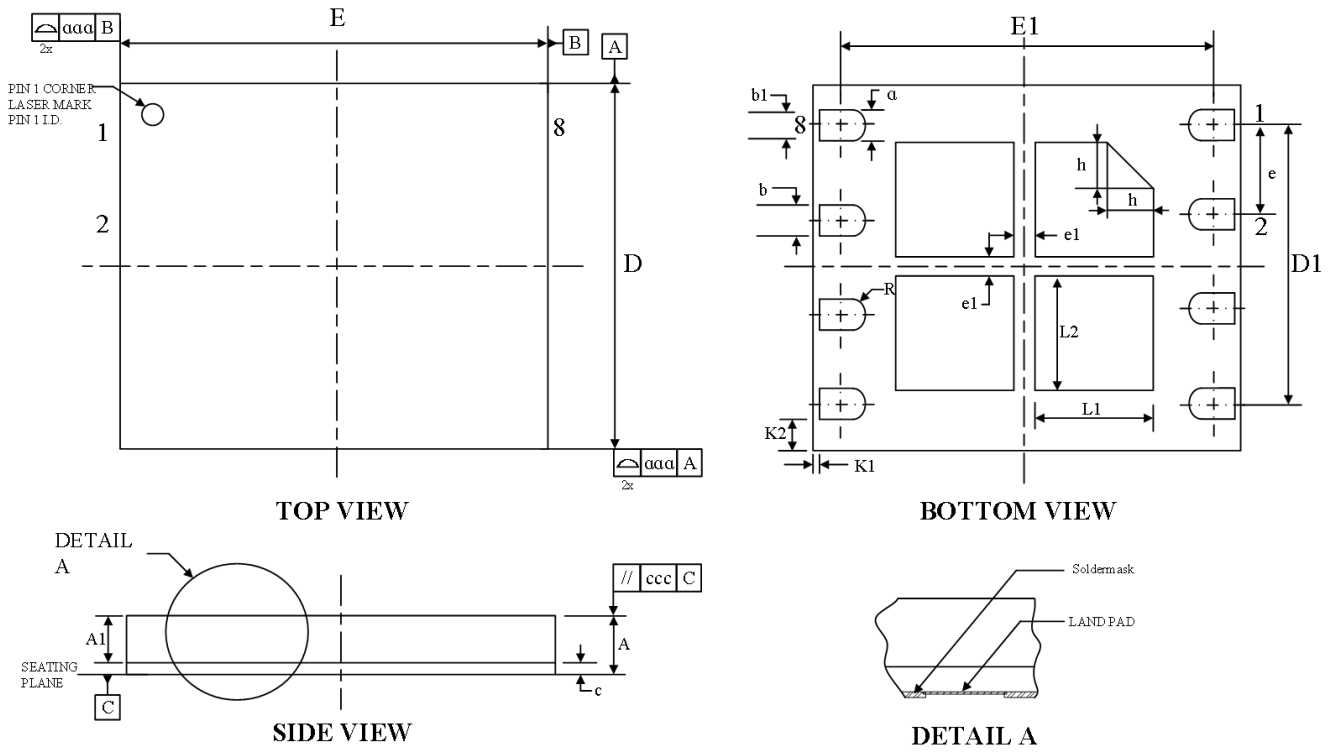
# 9. Package Information

## 9.1 Package WSON8 8x6mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.35	0.40	0.45
b1	0.25 REF		
c	0.18	0.20	0.25
D	5.90	6.00	6.10
Nd	3.81 BSC		
e	1.27 BSC		
E	7.90	8.00	8.10
D2	4.20	4.30	4.40
E2	3.30	3.40	3.50
L	0.45	0.50	0.55
h	0.30	0.35	0.40

### 9.2 Package LGA8 6x5mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.53 BASIC		
c	0.19	0.22	0.25
D	4.90	5.00	5.10
D1	3.81 BASIC		
E	5.90	6.00	6.10
E1	5.40 BASIC		
e	1.27 BASIC		
e1	0.40 BASIC		
a	0.55	0.60	0.65
b	0.35	0.40	0.45
b1	0.25 REF		
L1	1.30	1.80	2.30
L2	1.00	1.50	2.00
h	0.30	0.35	0.40
K1	0.100 REF		
K2	0.395 REF		
aaa	0.10		
ccc	0.20		



## 10. Revision History

Revision	Description	Date
0.1	Initial version	Jul 12, 2021
0.2	Update Standby Current Typ. value from 180uA to 130uA Update Standby Current Max. value from 450uA to 710uA Update Read/Write Current Typ. value from 25mA to 32mA Update Read/Write Current Typ. value from 40mA to 75mA	Nov 18, 2022
0.3	Update Standby Current Max. value from 710uA to 2500uA Add 1Gb/2Gb 1.8V LGA8(6x5mm)	Jun 05, 2023
0.4	Update XTSDG0xG VIL Max. value from 0.2VDD to 0.3VDD Update XTSDG0xG VOL Max. value from 0.125VDD to 0.4 Update XTSDG0xG VOH Min. value from 0.75VDD to VDD-0.3	Aug 28, 2023
0.5	Delete Interface Description Modify Package WSON8 thermal pad size	Jan 25, 2024